AMENDMENTS TO THE CLAIMS

Please amend Claims 1, 2, 7, 18 and 19 as follows. Insertions are shown underlined while deletions are ~~struck through~~. Please cancel Claims 5, 11-13 and 17.

1 (currently amended): A polishing pad used for chemical mechanical polishing ~~having~~ comprising:

a polishing region; and

a light-transmitting region ~~used in chemical mechanical polishing, wherein the light-transmitting region satisfies that the difference~~ constituted by a material having a ΔT of 10 (%) or less which is defined by the equation

~~($\Delta T = T_0 - T_1$)~~

wherein ΔT (%) is a difference between T_0 (%) and T_1 ~~is within 10~~ (%) as measured over the whole range of measurement wavelengths of from 400 to 700 nm, wherein T_1 is ~~the~~a light transmittance (%) of ~~t~~the material of he light-transmitting region as measured at the measurement wavelength λ after dipping the material in a KOH aqueous solution at pH 11 for 24 hours and T_0 is ~~the~~a light-transmittance (%) of the material as measured at the measurement wavelength λ before the dipping.

wherein the material of the light-transmitting region is formed from (i) polycaprolactone polyol, (ii) polyester polycarbonate polyol, or (iii) polyester polyol formed from adipic acid, hexane diol, and ethylene glycol.

2 (currently amended): A polishing pad used for chemical mechanical polishing ~~having~~ comprising:

a polishing region; and

a light-transmitting region ~~used in chemical mechanical polishing, wherein the light-transmitting region satisfies that the difference~~ constituted by a material having a ΔT of 10 (%) or less which is defined by the equation

~~($\Delta T = T_0 - T_1$)~~

wherein ΔT (%) is a difference between T_0 (%) and T_1 ~~is within 10~~ (%) as measured over the whole range of measurement wavelengths of from 400 to 700 nm, wherein T_1 is ~~the~~a light transmittance (%) of ~~t~~the material of he light-transmitting region as measured at the measurement wavelength λ after dipping the material in an H_2O_2

aqueous solution at pH 11 for 24 hours and T_0 is ~~the~~a light-transmittance (%) of the material as measured at the measurement wavelength λ before the dipping,

wherein the material of the light-transmitting region is formed from (i) polycaprolactone polyol, (ii) polyester polycarbonate polyol, or (iii) polyester polyol formed from adipic acid, hexane diol, and ethylene glycol.

3 (previously presented): The polishing pad according to claim 1, wherein the material forming the light-transmitting region is non-foam.

4 (previously presented): The polishing pad according to claim 1, wherein the material forming the polishing region is fine-cell foam.

5 (canceled):

6 (previously presented): The polishing pad according to claim 1, wherein the polishing region at the polishing side is provided with grooves.

7 (currently amended): A method of manufacturing a semiconductor device, which comprises:

(i) providing a polishing pad comprising:

a polishing region; and

a light-transmitting region constituted by a material having a ΔT of 10 (%) or less which is defined by the equation

$\Delta T = T_0 - T_1$

wherein ΔT (%) is a difference between T_0 (%) and T_1 (%) as measured over the whole range of measurement wavelengths of from 400 to 700 nm, wherein T_1 is a light transmittance (%) of the material of he light-transmitting region as measured at the measurement wavelength λ after dipping the material in a KOH aqueous solution at pH 11 for 24 hours and T_0 is a light-transmittance (%) of the material as measured at the measurement wavelength λ before the dipping,

wherein the material of the light-transmitting region is formed from (i) polycaprolactone polyol, (ii) polyester polycarbonate polyol, or (iii) polyester polyol formed from adipic acid, hexane diol, and ethylene glycol; and

(ii) ~~a step of~~ polishing the surface of a semiconductor wafer with the polishing pad ~~according to claim 1~~.

8 (previously presented): The polishing pad according to claim 2, wherein the material forming the light-transmitting region is non-foam.

9 (previously presented): The polishing pad according to 2, wherein the material forming the polishing region is fine-cell foam.

10 (previously presented): The polishing pad according to 3, wherein the material forming the polishing region is fine-cell foam.

11-13 (canceled):

14 (previously presented): The polishing pad according to claim 2, wherein the polishing region at the polishing side is provided with grooves.

15 (previously presented): The polishing pad according to claim 3, wherein the polishing region at the polishing side is provided with grooves.

16 (previously presented): The polishing pad according to claim 4, wherein the polishing region at the polishing side is provided with grooves.

17 (canceled):

18 (currently amended): A method of manufacturing a semiconductor device, which comprises:

(i) providing a polishing pad comprising:

a polishing region; and

a light-transmitting region constituted by a material having a ΔT of 10 (%) or less which is defined by the equation

$$\Delta T = T_0 - T_1$$

wherein ΔT (%) is a difference between T_0 (%) and T_1 (%) as measured over the whole range of measurement wavelengths of from 400 to 700 nm, wherein T_1 is a light transmittance (%) of the material of he light-transmitting region as measured at the measurement wavelength λ after dipping the material in an H_2O_2 aqueous solution at pH 11 for 24 hours and T_0 is a light-transmittance (%) of the material as measured at the measurement wavelength λ before the dipping,

wherein the material of the light-transmitting region is formed from (i) polycaprolactone polyol, (ii) polyester polycarbonate polyol, or (iii) polyester polyol formed from adipic acid, hexane diol, and ethylene glycol; and

(ii) ~~a step of~~ polishing the surface of a semiconductor wafer with the polishing pad ~~according to claim 2~~.

19 (currently amended): A polishing pad for chemical mechanical polishing comprising:

a polishing region having a through-hole in an axial direction; and

a light-transmitting region fitted in the through-hole, said light-transmitting region being constituted by a material having a ΔT of 10 (%) or less which is defined by the equation

$$\Delta T = T_0 - T_1$$

~~satisfying that~~wherein ΔT ~~which~~ is a difference between T_0 (%) and T_1 (%) ~~is within 10 percentage points~~ as measured over the whole range of measurement wavelengths of from 400 to 700 nm, wherein T_1 is a light transmittance (%)of the material of he light-transmitting region as measured at a measurement wavelength λ after dipping the material for 24 hours in a KOH aqueous solution having a pH of 11 or in an H_2O_2 aqueous solution having pH of 4, and T_0 is a light-transmittance (%) of the material as measured at the measurement wavelength λ before the dipping,

wherein the material of the light-transmitting region is formed from (i) polycaprolactone polyol, (ii) polyester polycarbonate polyol, or (iii) polyester polyol formed from adipic acid, hexane diol, and ethylene glycol.

20 (previously presented): The polishing pad according to claim 19, wherein the material forming the light-transmitting region is non-foam.

21 (previously presented): The polishing pad according to claim 19, further comprising a cushion layer laminated on a back side of the polishing region opposite to its polishing side, wherein the cushion layer has a through-hole at the same position as the light-transmitting region with respect to the axial direction.

22 (previously presented): The polishing pad according to claim 21, wherein the cushion layer is laminated on the polishing region using a double-coated tape.

23 (previously presented): The polishing pad according to claim 19, wherein the material is a polyurethane resin comprising an organic isocyanate, a polyol, and a chain extender.

24 (previously presented): The polishing pad according to claim 23, wherein in the polyurethane resin, a ratio of the number of isocyanate groups of the organic isocyanate to the number of functional groups of the polyol and the chain extender in total is 0.95 to 1.15.